

MSN50D603

V1.1 Datasheet

N-Channel 60V MOSFET

DFN3333

FEATURES

- ●Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

PRODUCTY SUMMARY							
V _{DS}	R _{DS(on)} m(Ω) Max						
60	54	@V _{GS} =10V					
60	60	@V _{GS} =4.5V					

Application

- Portable Devices
- Consumer Electronics

Mechanical

Case:DFN3333 Package

Packing Information

Package	Packing
DFN3333	5Kpcs/13"Reel

Maximum Ratings (T _A =25°C unless otherwise specified)							
Parameter	Symbol	Limit	Unit				
Drain-Source Voltage	V _{DS}	60	V				
Gate-Source Voltage	V _{GS}	±20	V				
Continuous Drain Current ¹⁾	I _D	10	А				
Continuous Drain Current ⁴⁾	I _{DM}	40	А				
Maximum Power Dissipation	P _D	5	W				
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C				

Typical Thermal Resistance						
Parameter Symbol Limit Unit						
Junction-to-Ambient Thermal Resistance 3)	$R_{ extsf{ heta}JA}$	34	°C/W			

Note:

1. Pulse width<300us, Duty cycle<2%.

^{2.} Fused current that based on wire numbers and diameter.

^{3.} Guaranteed by design, not subject to production testing.

^{4.} The maximum current rating is package limited.

^{5.} Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150$ °C. Ratings are based on low frequency and duty cycles to keepinitial $T_J = 25$ °C.



Electrical Characteristics ($T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)							
Characteristics	Symbol	Test Condition		Limits	Unit		
	Symbol		Min	Тур	Max	Unit	
Static							
Drain-Source Breakdown Voltage	B _{VDSS}	V_{GS} =0V, I _D =250uA	60	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250$ uA	1.0	1.7	3.0	V	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =10A	-	42	54	mΩ	
		V _{GS} =4.5V, I _D =9A	-	45	60	mΩ	
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =60V, V_{GS} =0V	-	-	1	uA	
GateSource Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA	

Dynamic ³⁾							
Total Gate Charge	Q _g		-	2	-	nC	
GateSource Charge	Q_gs	V_{DS} =30V, V_{GS} =4.5V, I _D =5.3A ^(Note 1,2)	-	3	-	nC	
GateDrain Charge	Q_gd		-	6	-	nC	
Input Capacitance	C _{iss}	V _{DS} =30V, V _{GS} =0V, f=200KHz	-	714	-	pF	
Output Capacitance	C _{oss}		-	54	-	pF	
Reverse Transfer Capacitance	C _{rss}		-	38	-	pF	

Switching							
TurnOn Delay Time	t _{d(on)}	N 20V	-	17	-	ns	
TurnOn Rise Time	t _r	V _{DS} =30V, Vgen=4.5V,	-	18	-	ns	
TurnOff Delay Time	t _{d(off)}	I _D =5A , Rg=1Ohm	-	24	-	ns	
TurnOff Fall Time	t _f	Kg=101illi	-	7	-	ns	

DrainSource Diode						
Maximum Continuous Body Diode Forward Current	I _S	-	-	-	1.2	А
Diode Forward Voltage	V_{SD}	I _S =1.0A, V _{GS} =0V	-	-	1.5	V

Note:

1. Pulse width<300us, Duty cycle<2%.

2. Essentially independent of operating temperature typical characteristics.

3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150$ °C. Ratings are based on low frequency and duty cycles to keep initial $T_J = 25$ °C.

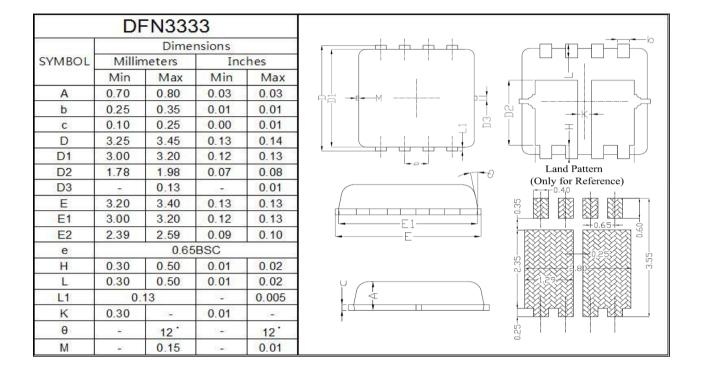
4. The maximum current rating is package limited.

5. R_{QJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch2 with 2oz.square pad of copper.

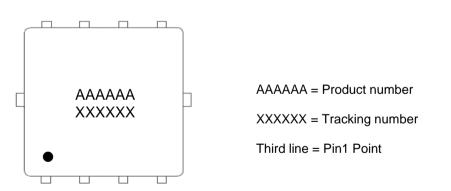
6. Guaranteed by design, not subject to production testing.



Package Outline Dimensions (inches and millimeters)



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